Low-Voltage CMOS Octal D-Type Flip-Flop Flow Through Pinout

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX574 is a high performance, non–inverting octal D–type flip–flop operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX574 inputs to be safely driven from 5.0 V devices.

The MC74LCX574 consists of 8 edge—triggered flip—flops with individual D—type inputs and 3—state true outputs. The buffered clock and buffered Output Enable (\overline{OE}) are common to all flip—flops. The eight flip—flops will store the state of individual D inputs that meet the setup and hold time requirements on the LOW—to—HIGH Clock (CP) transition. With the \overline{OE} LOW, the contents of the eight flip—flops are available at the outputs. When the \overline{OE} is HIGH, the outputs go to the high impedance state. The \overline{OE} input level does not affect the operation of the flip—flops. The LCX574 flow through design facilitates easy PC board layout.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V

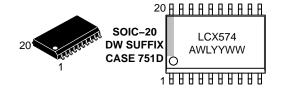
Machine Model >200 V

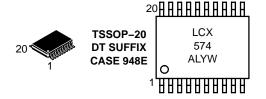
• Pb-Free Packages are Available*

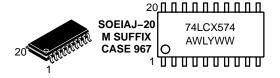


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MARKING DIAGRAMS







A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

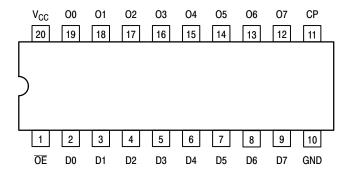


Figure 1. Pinout: 20-Lead (Top View)

ŌΕ nCP 00 2 D0 D nCP 01 3 D1 nCP 02 4 D2 D nCP 5 D3 nCP 04 6 nCP 05 7 Q D 13 nCP 06 8 D6 D 12 nCP 9 07 D7

Figure 2. LOGIC DIAGRAM

PIN NAMES

Function
Output Enable Input Clock Pulse Input
Data Inputs 3–State Outputs

TRUTH TABLE

	INPUTS		INTERNAL LATCHES	OUTPUTS	
ŌĒ	СР	Dn	Q	On	OPERATING MODE
L L	↑	l h	L H	L H	Load and Read Register
L	1	Х	NC	NC	Hold and Read Register
Н	1	Х	NC	Z	Hold and Disable Outputs
H H	<u></u>	l h	L H	Z Z	Load Internal Register and Disable Outputs

H = High Voltage Level

h = High Voltage Level One Setup Time Prior to the Low-to-High Clock Transition

L = Low Voltage Level

I = Low Voltage Level One Setup Time Prior to the Low-to-High Clock Transition

NC = No Change

X = High or Low Voltage Level and Transitions are Acceptable

Z = High Impedance State ↑ = Low-to-High Transition

1 = Not a Low-to-High Transition; For I_{CC} Reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State) (3–State)	0		V _{CC} 5.5	٧
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0 V - 3.6 V			-24	mA
I _{OL}	LOW Level Output Current, V _{CC} = 3.0 V – 3.6 V			24	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.7 V – 3.0 V			-12	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.7 V - 3.0 V			12	mA
T _A	Operating Free–Air Temperature			+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX574DWR2	SOIC-20	1000 Tape & Reel
MC74LCX574DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX574DT	TSSOP-20*	75 Units / Rail
MC74LCX574DTR2	TSSOP-20*	2000 Tape & Reel
MC74LCX574MEL	SOEIAJ-20	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		V
V _{IL}	LOW Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	V
V _{OH}	HIGH Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V _{CC} – 0.2		V
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2		1
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		1
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		1
V _{OL}	LOW Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
IĮ	Input Leakage Current	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5.0	μΑ
I _{OZ}	3-State Output Current	$2.7 \le V_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or V }_{IL}$		±5.0	μΑ
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 \text{ V; } V_{I} \text{ or } V_{O} = 5.5 \text{ V}$		10	μΑ
I _{CC}	Quiescent Supply Current	$2.7 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.7 \le V_{CC} \le 3.6 \text{ V}$; $3.6 \le V_I \text{ or } V_O \le 5.5 \text{ V}$	1	±10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.7 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω)

				Lim	nits		
				T _A = −40°C	C to +85°C		
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
f _{max}	Clock Pulse Frequency	1	150				MHz
t _{PLH} t _{PHL}	Propagation Delay CP to On	1	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t _{PZH} t _{PZL}	Output Enable Time to HIGH and LOW Levels	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t _{PHZ}	Output Disable Time from HIGH and LOW Levels	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns
t _s	Setup Time, HIGH or LOW Dn to CP	1	2.5		2.5		ns
t _h	Hold Time, HIGH or LOW Dn to CP	1	1.5		1.5		ns
t _w	CP Pulse Width, HIGH or LOW	3	3.3		3.3		ns
toshl toslh	Output-to-Output Skew (Note 3)			1.0 1.0			ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

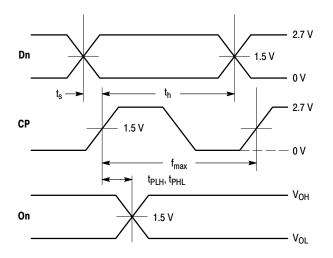
DYNAMIC SWITCHING CHARACTERISTICS

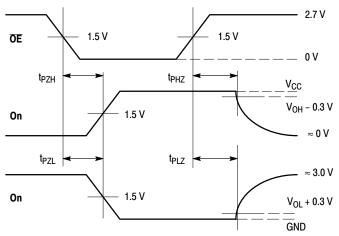
			T,	_A = +25°	С	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Parameter Condition		Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	7	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF



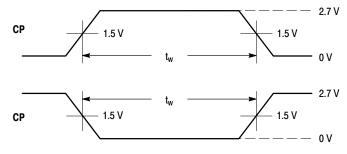


WAVEFORM 1 - PROPAGATION DELAYS, SETUP AND HOLD TIMES

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

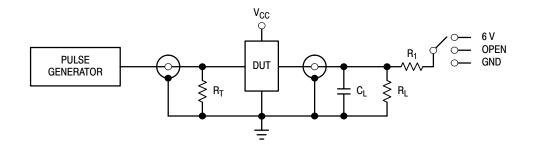
 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 3 - PULSE WIDTH

 t_R = t_F = 2.5 ns (or fast as required) from 10% to 90%; Output requirements: $V_{OL} \le 0.8$ V, $V_{OH} \ge 2.0$ V

Figure 3. AC Waveforms



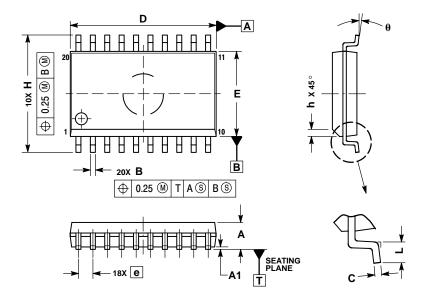
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

 C_L = 50 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



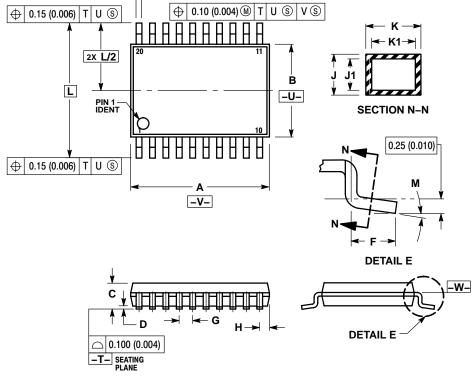
20X **K** REF

NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- PROTRUSION: MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



NOTES:

- DTES:

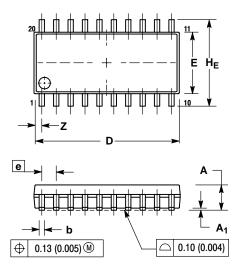
 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER
 SIDE
- SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR FOR THOSING STALL BOOM (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 3. TERMINAL NUMBERS ARE SHOWN
- FOR REFERENCE ONLY.

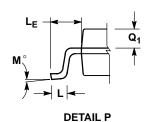
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

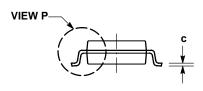
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ĺ	6.40	BSC	0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLIDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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